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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/002,035	11/01/2001	Jeffrey W. Carr	RAPT-01000US1	5043
23910 FLIESLER ME	7590 03/26/2007 EYER LLP.		EXAM	INER
650 CALIFORNIA STREET OLSEN, ALLAN W			LLAN W	
14TH FLOOR SAN FRANCI	SCO, CA 94108		ART UNIT PAPER NUMBER 1763	
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SHORTENED STATUTOR	RY PERIOD OF RESPONSE	MAIL DATE	DELIVERY MODE	
3 MO	ONTHS	03/26/2007	PAPER	

Please find below and/or attached an Office communication concerning this application or proceeding.

If NO period for reply is specified above, the maximum statutory period will apply and will expire 6 MONTHS from the mailing date of this communication.

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	Application No.	Applicant(s)	•
	10/002,035	CARR, JEFFREY W.	
Office Action Summary	Examiner	Art Unit	
	Allan Olsen	1763	
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the c	correspondence addre	ss
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a repl - If NO period for reply is specified above, the maximum statutory period of Failure to reply within the set or extended period for reply will, by statute - Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be ting within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from a cause the application to become ABANDONE	nely filed rs will be considered timely. the mailing date of this commi	unication.
Status	January 2007		
1) Responsive to communication(s) filed on 11.			
, <u> </u>	is action is non-final.	rango tian an ta tha m	arita ia
 Since this application is in condition for allowed closed in accordance with the practice under Disposition of Claims 			ierits is
4)⊠ Claim(s) <u>3-15,18-21,32,37,39,41,42,44-60,62</u>	,64 and 66 is/are pending in the a	application.	
4a) Of the above claim(s) <u>41,42,46,50,54 and s</u>			
5) Claim(s) is/are allowed.			
6) Claim(s) <u>3-15,18-21,32,37,39,44,45,47-49,51-</u>	53,55-57,59,60,62,64 and 66 is/a	re rejected.	
7) Claim(s) is/are objected to.			
8) Claim(s) are subject to restriction and/o	r election requirement.		
Application Papers			
9) The specification is objected to by the Examine	r.		
10) The drawing(s) filed on 09 May 2002 is/are: a)	☑ accepted or b)☐ objected to by the	ne Examiner.	
Applicant may not request that any objection to the			
11)☐ The proposed drawing correction filed on	_ is: a)□ approved b)□ disappro	oved by the Examiner.	
If approved, corrected drawings are required in re	•		
12) The oath or declaration is objected to by the Ex	aminer.		
Priority under 35 U.S.C. §§ 119 and 120		•	
13) Acknowledgment is made of a claim for foreign	n priority under 35 U.S.C. § 119(a	ı)-(d) or (f).	
a) ☐ All b) ☐ Some * c) ☐ None of:			
 Certified copies of the priority document 	s have been received.		
2. Certified copies of the priority document	s have been received in Applicati	on No	
3. Copies of the certified copies of the prior application from the International Bu * See the attached detailed Office action for a list	reau (PCT Rule 17.2(a)).		ge
14)⊠ Acknowledgment is made of a claim for domesti	·		olication)
a) The translation of the foreign language pro	ovisional application has been rec	eived.	
15) Acknowledgment is made of a claim for domest Attachment(s)	ic priority under 35 U.S.C. 99 120	anu/or 121.	
Notice of References Cited (PTO-892)	4) Intentious Summer	/ (PTO-413) Paper No(s)	
Notice of References Cited (P10-692) Notice of Draftsperson's Patent Drawing Review (PT0-948) Information Disclosure Statement(s) (PT0-1449) Paper No(s) 2	5) Notice of Informal F	Patent Application (PTO-15	

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DETAILED ACTION

A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on January 11, 2007 has been entered.

All claims are rejected for reasons of record. The rejections as set forth in the Final Office action of August 14, 2006 are repeated below.

All claims are drawn to the same invention claimed in the application prior to the entry of the submission under 37 CFR 1.114 and could have been finally rejected on the grounds and art of record in the next Office action if they had been entered in the application prior to entry under 37 CFR 1.114. Accordingly, **THIS ACTION IS MADE FINAL** even though it is a first action after the filing of a request for continued examination and the submission under 37 CFR 1.114. See MPEP § 706.07(b).

Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of

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the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Claim Rejections - 35 USC § 103

Claims 3, 5-12, 18, 20, 21, 32, 37, 39, 44, 45, 47-49, 51-53, 55, 60, 62, 64 and 66 are rejected under 35 U.S.C. 102(b) as being anticipated by Zarowin et al. in Rapid, Non-Contact, Damage Free Shaping of Optical & Other Surfaces with Plasma Assisted Chemical Etching, 43rd Annual Symposium on Frequency Control 1989, 623-626 (hereinafter, Zarowin) in view of Böhm et al. in DE 199 25 790 (hereinafter, Böhm)

Zarowin teaches using a reactive atom plasma to provide a damage free and contamination free, shaped optical surface. Because the annulus center of Zarowin's annular plasma is continually supplied with a reactive species such as CF₄ and SF₆, Zarowin is considered to teach "injecting a flow of a species into the annulus center of the annular plasma to create at least one reactive species". Zarowin teaches controlling the flow of plasma gases to adjust the balance between etching and deposition processes. See: figures 1, 2 and 9; also, the 2nd and 4th paragraphs on page 623 and the 1st paragraph on page 624.

Zarowin does not teach supplying a separate flow of a precursor into the annulus center of an annular plasma.

Böhm teaches supplying a separate flow of a precursor into the annulus center of an annular plasma.

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It would have been obvious to one skilled in the art to provide a separate flow of reactive species into the core of the Zarowin's plasma because Böhm teaches that this gas inlet scheme provides a plasma with an inert sheath so reactive species do not make contact with components of the plasma system thereby eliminating a source of contamination (see paragraph bridging pages 4 and 5 of the translation).

Claims 3-12, 19-21, 32, 37, 39, 44, 45, 47-49, 51, 60, 62, 64 and 66 are rejected under 35 U.S.C. 103(a) as being unpatentable over Bollinger et al. in "Rapid, Non-Contact Optical Figuring of Aspheric Surfaces with Plasma Assisted Chemical Etching (PACE)" in SPIE Vol. 1333 page 44-57 (hereinafter, Bollinger) in view of Zarowin and further in view of Böhm.

As the title of the paper indicates, Bollinger teaches using a reactive atom plasma to shape aspherical optical surfaces. Bollinger teaches supplying the plasma reactive species such as CF₄ and SF₆. Bollinger teaches removing damage introduced by previous process steps. See: pages 44 - 47, 51, 52 and 57.

Bollinger does not teaches an annular plasma.

Zarowin teaches an annular plasma.

Zarowin does not teach supplying a separate flow of a precursor into the annulus center of an annular plasma.

Böhm teaches supplying a separate flow of a precursor into the annulus center of an annular plasma.

It would have been obvious to one skilled in the art to carry out Bollinger's process with an annular plasma while providing a separate flow of reactive species into

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the core of the annular plasma because it is readily apparent that the system and process of Bollinger and Zarowin are essentially the same and Bollinger's complete silence with regard to the plasma footprint suggests that the footprints taught by figure 2 of Zarowin are applicable to the process of Bollinger. It would have been obvious to one skilled in the art to provide a separate flow of reactive species into the core of the plasma because Böhm teaches that this gas inlet scheme provides a plasma with an inert sheath so reactive species do not make contact with components of the plasma system thereby eliminating a source of contamination (see paragraph bridging pages 4 and 5 of the translation).

Claims 13-15, 56, 57 and 59 are rejected under 35 U.S.C. 103(a) as being unpatentable over Bollinger in view of US Patent 5,961,772 issued to Selwyn, in view of Böhm and further in view of US Patent 6,068,784 issued to Collins et al. (hereinafter, Collins).

The above noted teachings of Bollinger are herein relied upon.

Bollinger does not teach using Ar. Bollinger does not teach operating near atmospheric pressure.

Selwyn teaches that the provision of a high flow rate of argon enables one to carry out a process similar to that of Bollinger's at atmospheric pressure rather than at the low pressure taught by Bollinger. For example, Selwyn teaches etching SiO_2 with a room temperature, atmospheric pressure plasma wherein the plasma gases comprise CF_4 and Ar.

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Selwyn does not teach providing a separate flow of the reactive precursor into the annulus center of an annular plasma.

Böhm teaches supplying a separate flow of a precursor into the annulus center of an annular plasma.

It would have been obvious to one skilled in the art to carry out Bollinger's process by adding the CF₄ or SF₆ to the annulus center of an annular inert gas plasma because Selwyn teaches that the by adding Ar to CF₄ or SF₆ plasma of Bollinger enables one to operate the system at atmospheric pressure which greatly simplifies the operational demands of the process and Selwyn demonstrates that etch rates for process carried out at atmospheric pressure are greater than those carried out under a typical low pressure condition. Furthermore, it would have been obvious to one skilled in the art to provide a separate flow of Bollinger's reactive species, CF4 or SF₆, into the core of an annular inert plasma because Böhm teaches that this gas inlet scheme provides a plasma with an inert sheath thereby preventing reactive species from making contact with components of the plasma system and eliminating a source of contamination (see paragraph bridging pages 4 and 5 of the translation).

Bollinger and Selwyn do not teach using C_2F_6 to etch SiO₂.

Collins teaches using C_2F_6 to etch SiO₂.

It would have been obvious to one skilled in the art to use C₂F₆ in place of CF₄ to etch SiO₂ because Collins teaches that CF₄ and C₂F₆ are functionally equivalent as a fluorocarbon etchant of SiO₂.

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Response to Arguments

As set forth in the Advisory action of December 15, 2006:

Applicant's arguments filed November 14, 2006 have been fully considered but they are not persuasive.

Applicant argues that by their method, reactive species are generated by exciting a precursor "with a radio frequency (RF) power via the annular plasma" whereas in the applied art, reactive species are generated by directly exciting a precursor with an applied electromagnetic radiation. Applicant's reliance on an intermediary annular plasma as a means of transferring energy to the precursor may very well facilitate a shift from a direct excitation to an indirect excitation. Nevertheless, the applied references teach injecting a precursor into an annular plasma whereby at least some indirect excitation of the precursor will occur.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Allan Olsen whose telephone number is 571-272-1441. The examiner can normally be reached on M, W and F: 1-5.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Parviz Hassanzadeh can be reached on 571-272-1435. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Alla Olan

Allan Olsen Primary Examiner Art Unit 1763